74LVC1G10

Single 3-input NAND gate

Rev. 01 — 2 October 2007

Product data sheet

1. General description

The 74LVC1G10 provides a low-power, low-voltage single 3-input NAND gate.

The inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall time.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V).
- \pm 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101-C exceeds 1000 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering information

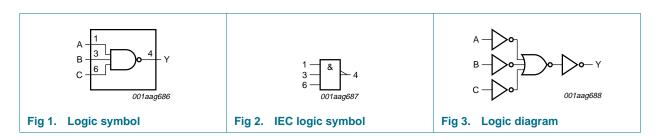
Type number	Package	Package						
	Temperature range	Name	Description	Version				
74LVC1G10GW	-40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363				
74LVC1G10GV	−40 °C to +125 °C	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457				
74LVC1G10GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1\times1.45\times0.5$ mm	SOT886				
74LVC1G10GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1 \times 0.5$ mm	SOT891				

4. Marking

Table 2. Marking

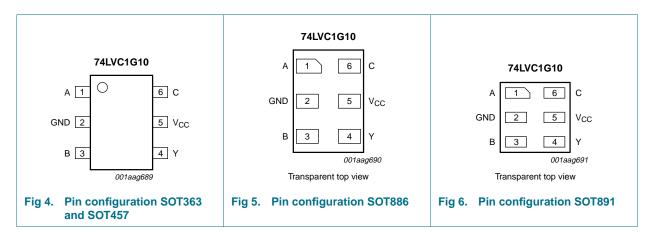
Type number	Marking code
74LVC1G10GW	YM
74LVC1G10GV	YM
74LVC1G10GM	YM
74LVC1G10GF	YM

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
A	1	data input
GND	2	ground (0 V)
В	3	data input
Υ	4	data output
V _{CC}	5	supply voltage
С	6	data input

7. Functional description

Table 4. Function table[1]

Input	Output		
Α	В	С	Υ
Н	Н	Н	L
L	X	X	Н
X	L	X	Н
X	X	L	Н

^[1] H = HIGH voltage level;

L = LOW voltage level;

X = don't care.

Limiting values

Limiting values Table 5.

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
I _{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0 V$	-	±50	mA
V_{O}	output voltage	Active mode	[1][2] -0.5	$V_{CC} + 0.5$	V
		Power-down mode	[1][2] -0.5	+6.5	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±50	mA
I _{CC}	supply current		-	100	mA
I_{GND}	ground current		-100	-	mA
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[3]</u> _	250	mW
T _{stg}	storage temperature		-65	+150	°C

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

Recommended operating conditions

Table 6. **Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
V_{I}	input voltage		0	-	5.5	V
Vo	output voltage	Active mode	0	-	V_{CC}	V
		Power-down mode; V _{CC} = 0 V	0	-	5.5	V
T _{amb}	ambient temperature		-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	-	-	20	ns/V
		$V_{CC} = 2.7 \text{ V to } 5.5 \text{ V}$	-	-	10	ns/V

^[2] When $V_{CC} = 0 \text{ V}$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

^[3] For SC-88 and SC-74A packages: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K. For XSON6 packages: above 45 $^{\circ}\text{C}$ the value of Ptot derates linearly with 2.4 mW/K.

10. Static characteristics

Static characteristics Table 7.

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol Parameter		Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65V _{CC}	-	-	0.65V _{CC}	-	V
	voltage	V _{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
		V _{CC} = 4.5 V to 5.5 V	$0.7V_{CC}$	-	-	$0.7V_{CC}$	-	V
V_{IL}	LOW-level input	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	-	-	$0.35V_{CC}$	-	0.35V _{CC}	V
	voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	-	0.7	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	-	8.0	-	8.0	V
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	V
V_{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}						
	output voltage	$I_O = -100 \mu A;$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	V _{CC} – 0.1	-	-	V _{CC} – 0.1	-	V
		$I_O = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	0.95	-	V
		$I_O = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	1.7	-	V
		$I_O = -12$ mA; $V_{CC} = 2.7$ V	2.2	-	-	1.9	-	V
		$I_O = -24$ mA; $V_{CC} = 3.0$ V	2.3	-	-	2.0	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.8	-	-	3.4	-	V
V_{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_O = 100 \mu A;$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	-	0.10	-	0.10	V
		$I_O = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.45	-	0.70	V
		$I_O = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.30	-	0.45	V
		$I_O = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.40	-	0.60	V
		$I_O = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	-	0.80	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	-	0.80	V
I _I	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to 5.5 V}$	-	±0.1	±5	-	±100	μΑ
l _{OFF}	power-off leakage current	V_I or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	±0.1	±10	-	±200	μΑ
I _{CC}	supply current	$V_I = 5.5 \text{ V or GND}; I_O = 0 \text{ A};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	0.1	10	-	200	μΑ
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V} \text{ to } 5.5 \text{ V}; \text{ per pin}$	-	5	500	-	5000	μΑ
Cı	input capacitance	$V_{CC} = 3.3 \text{ V};$ $V_I = \text{GND to } V_{CC}$	-	3	-	-	-	pF

^[1] All typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Dynamic characteristics Table 8.

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 8.

Symbol	Parameter	Conditions		-40 °C to +85 °C			–40 °C to	+125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
t _{pd} propagation delay		A, B and C to Y; see Figure 7	[2]						
	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.5	4.7	18.0	1.5	21.5	ns	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.0	3.0	6.5	1.0	7.8	ns
		$V_{CC} = 2.7 \text{ V}$		1.0	3.0	6.0	1.0	7.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	2.6	5.0	1.0	6.2	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		1.0	1.9	3.6	1.0	4.4	ns
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}; V_{CC} = 3.3 \text{ V}$	[3]	-	12	-	-	-	pF

^[1] Typical values are measured at $T_{amb} = 25$ °C and $V_{CC} = 1.8$ V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

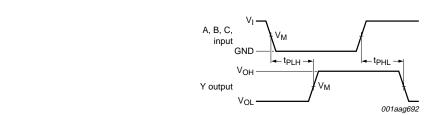
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



Measurement points are given in Table 9.

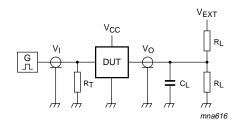
V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. The input (A, B, C) to output (Y) propagation delays

^[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

Table 9. **Measurement points**

Supply voltage	Input	Output
V _{CC}	V _M	V _M
1.65 V to 1.95 V	0.5V _{CC}	0.5V _{CC}
2.3 V to 2.7 V	0.5V _{CC}	0.5V _{CC}
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	0.5V _{CC}	0.5V _{CC}



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 8. Load circuit for switching times

Table 10. Test data

Supply voltage	Input	Input			V _{EXT}
V _{CC}	VI	$t_r = t_f$	CL	R _L	t _{PLH} , t _{PHL}
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	$500~\Omega$	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	$500~\Omega$	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	$500~\Omega$	open
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	open

13. Package outline

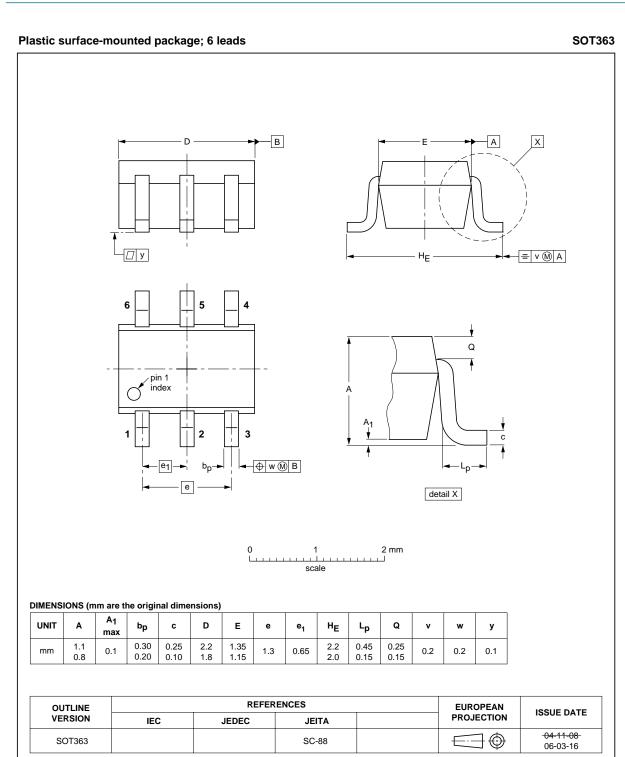


Fig 9. Package outline SOT363 (SC-88)

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Plastic surface-mounted package (TSOP6); 6 leads

SOT457

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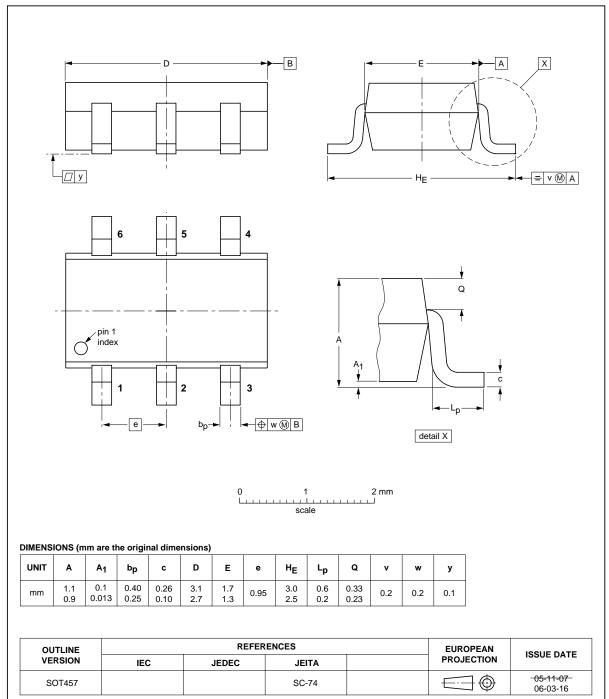


Fig 10. Package outline SOT457 (SC-74)

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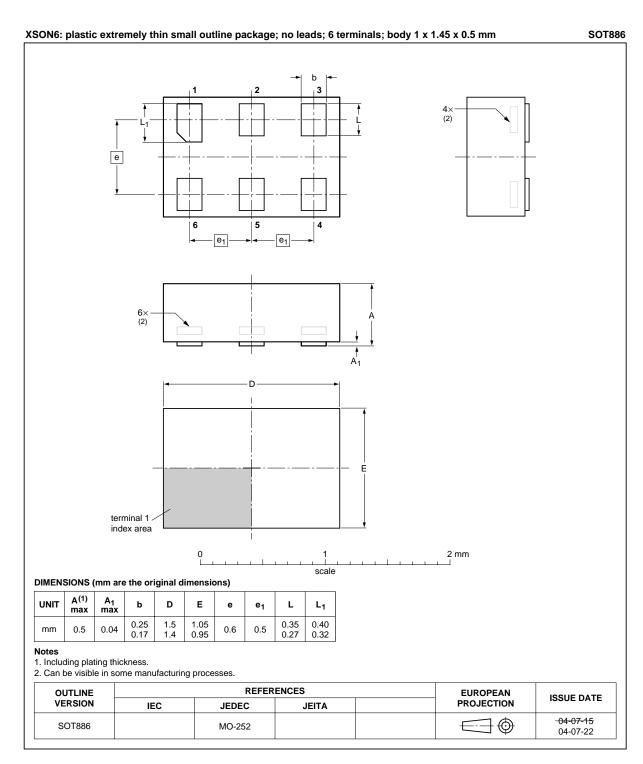


Fig 11. Package outline SOT886 (XSON6)

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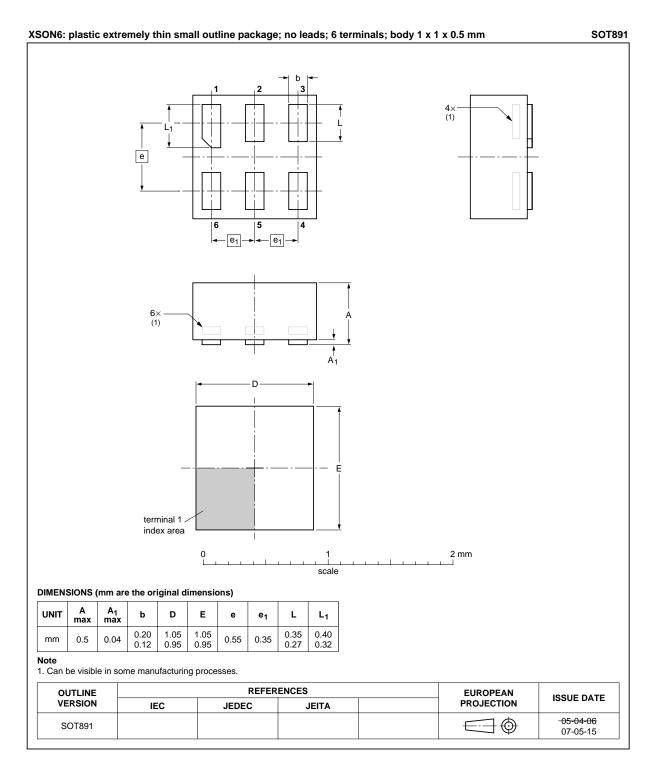


Fig 12. Package outline SOT891 (XSON6)

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Single 3-input NAND gate

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G10_1	20071002	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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